

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	451	LDMOS or (Lateral adj Double adj diffused adj (MOS))	USPAT ; USOCR ; EPO; JPO; Derwe nt	2000/12/1 4 12:43
2	BRS	L2	427	LDMOS or (Lateral adj Double adj diffused adj (MOS)) and (drift adj region) and different adj depth	USPAT ; USOCR ; EPO; JPO; Derwe nt	2000/12/1 4 12:47
3	BRS	L3	427	LDMOS or (Lateral adj Double adj diffused adj (MOS)) and (drift adj region) and different adj depth and (high adj breakdown adj voltage)	USPAT ; USOCR ; EPO; JPO; Derwe nt	2000/12/1 4 13:46

PATENTS OF INST

- 1) 5,286,995-
- 2) 5,583,365-
- 3) 5,382,536-
- 4) 5,917,222-
- 5) 5,242,841-

	Comments	Error Definition	Errors
1			0
2			0
3			0